

isc N-Channel MOSFET Transistor

FDA28N50

• FEATURES

- With TO-3PN packaging
- High speed switching
- Standard level gate drive
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

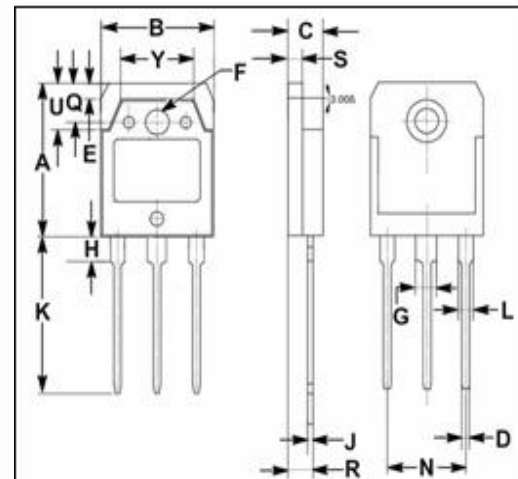
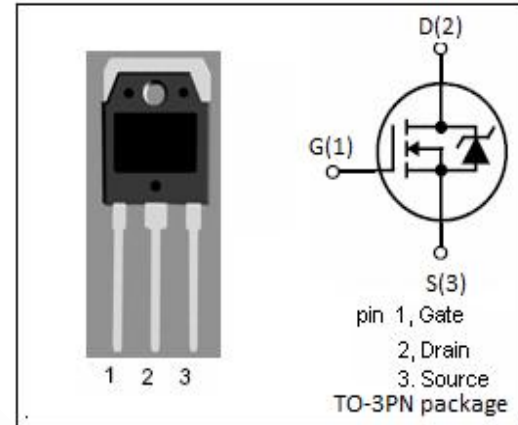
- Power supply
- Switching applications

• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	500	V
V _{GSS}	Gate-Source Voltage	±30	V
I _D	Drain Current-Continuous@T _c =25°C T _c =100°C	28 17	A
I _{DM}	Drain Current-Single Pulsed	112	A
P _D	Total Dissipation	310	W
T _j	Operating Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature	-55~150	°C

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th(ch-c)}	Channel-to-case thermal resistance	0.4	°C/W
R _{th(ch-a)}	Channel-to-ambient thermal resistance	40	°C/W



DIM	mm	
	MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =0.25mA	500			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =±30V; I _D =0.25mA	2.0		5.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =14A		0.12	0.15	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 500V; V _{GS} = 0; T _J =25°C V _{DS} = 400V; V _{GS} = 0; T _J =125°C			1 10	μA
V _{SDF}	Diode forward voltage	I _{SD} =28A, V _{GS} = 0 V			1.4	V